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SEMICONDUCTOR



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PLED

1N4001WS-1N4007WS

Product specification


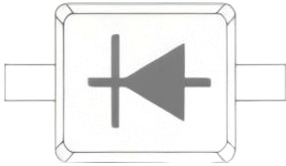
FEATURES

- Low profile space
- Ideal for automated placement
- Glass passivated chip junctions
- Low forward voltage drop
- Low leakage current
- High forward surge capability
- High temperature soldering : 260C/10 seconds at terminals

MECHANICAL DATA

- **Case:** SOD-323 molded plastic body over glass passivated chip
- **Terminals:** Solder plated, solderable per JESD22-B102
- **Polarity:** Laser band denotes cathode end

Reference News

| PACKAGE OUTLINE | Circuit | PINNING | |
|---|--|---------|-------------|
| | | PIN | DESCRIPTION |
|  <p>SOD-323</p> |  | 1 | Cathode |
| | | 2 | Anode |

Maximum Ratings & Thermal Characteristics

(TA = 25 °C unless otherwise noted).

| Items | Symbol | 1N4001WS 1 A | 1N4002WS 2 A | 1N4003WS 3 A | 1N4004WS 4 A | 1N4005WS 5 A | 1N4006WS 6 A | 1N4007WS 7 A | UNIT |
|--|-------------------|-----------------|-----------------|-----------------|-----------------|-----------------|-----------------|-----------------|--------|
| Maximum repetitive peak reverse voltage | V _{RRM} | 50 | 100 | 200 | 400 | 600 | 800 | 1000 | V |
| Maximum RMS voltage | V _{RMS} | 35 | 70 | 140 | 280 | 420 | 560 | 700 | V |
| Maximum DC blocking voltage | V _{DC} | 50 | 100 | 200 | 400 | 600 | 800 | 1000 | V |
| Maximum average forward rectified current at T _L = 90 °C | F _(AV) | 1 | | | | | | | A |
| Peak forward surge current 8.3 ms single half sine-wave superimposed on rated load | I _{FSM} | 25 | | | | | | | A |
| Thermal resistance from junction to lead(1) | R _{θ JL} | 35 | | | | | | | °C / W |
| Operating junction range | T _J | -55 to +150 | | | | | | | °C |
| Storage temperature range | T _{STG} | -55 to +150 | | | | | | | °C |

Note 1: Mounted on PCB with 0.2 x 0.2" (5.0 x 5.0mm) copper pad areas .

Electrical Characteristics(TA = 25 °C unless otherwise noted)

| Items | Test conditions | Symbol | Min | Type | Max | UNIT |
|-------------------------------|----------------------------------|----------------|-----|------------------------|-----|------|
| Instantaneous forward voltage | I _F = 0 .5A | V _F | - | 0.92 | - | V |
| | I _F = 1 A | | | 0.98 | 1.1 | |
| Reverse current | V _R = V _{DC} | I _R | | | 5 | μ A |
| | | | | T _A = 25 °C | | |
| | T _A = 125 °C | | | | | |

Note 2: Pulse test: 300 ps pulse width, 1% duty cycle.

RATING AND CHARACTERISTIC CURVES (1N4001WS THRU 1N4007WS)

Fig.1 Forward Current Derating Curve

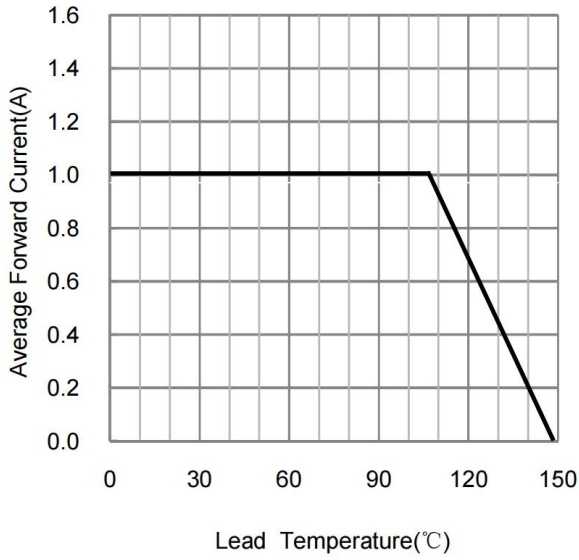


Fig.2 Maximum Non-Repetitive Peak Forward Surge Current

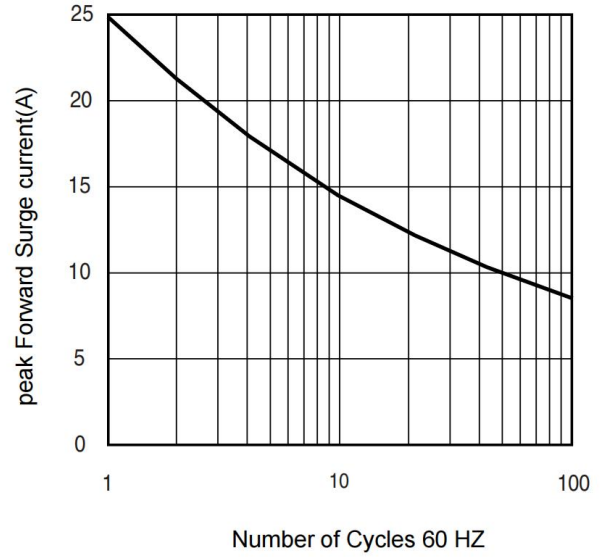


Fig.3 Typical Instantaneous Forward Characteristics

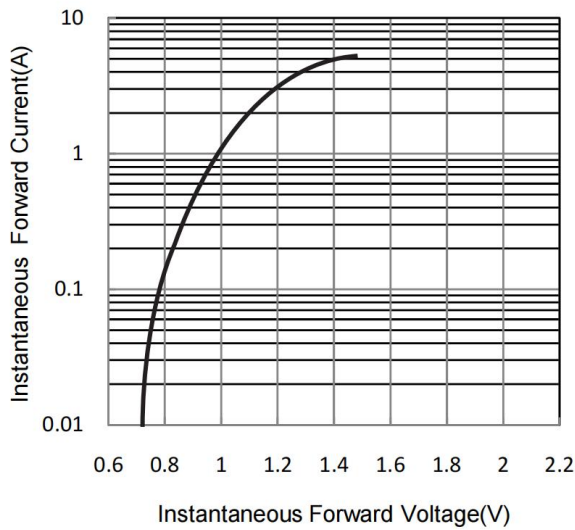
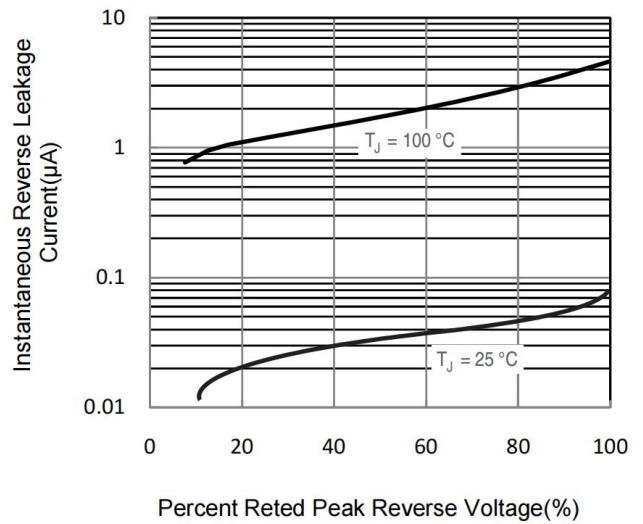
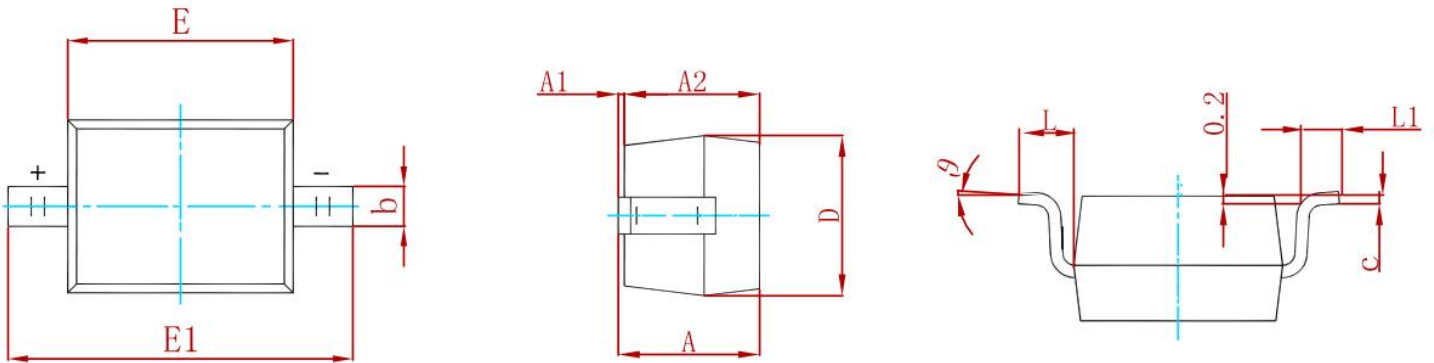


Fig.4 Typical Reverse Leakage Characteristics

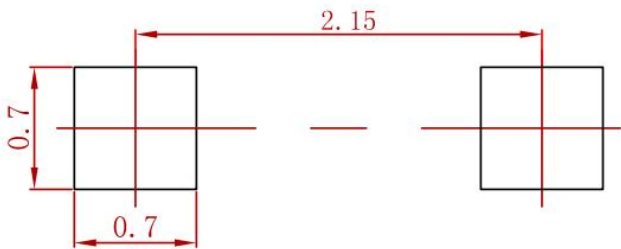


PACKAGE MECHANICAL DATA



| Symbol | Dimensions In Millimeters | | Dimensions In Inches | |
|--------|---------------------------|-------|----------------------|-------|
| | Min | Max | Min. | Max |
| A | | 1.000 | | 0.039 |
| A1 | 0.000 | 0.100 | 0.000 | 0.004 |
| A2 | 0.800 | 0.900 | 0.031 | 0.035 |
| b | 0.250 | 0.350 | 0.010 | 0.014 |
| C | 0.080 | 0.150 | 0.003 | 0.006 |
| D | 1.200 | 1.400 | 0.047 | 0.055 |
| E | 1.600 | 1.800 | 0.063 | 0.071 |
| E1 | 2.550 | 2.750 | 0.100 | 0.108 |
| L | 0.475 REF | | 0.019 REF | |
| L1 | 0.250 | 0.400 | 0.010 | 0.016 |
| θ | 0° | 8° | 0° | 8° |

Suggested Pad Layout



Note:

1. Controlling dimension: in millimeters.
2. General tolerance: ±0.05mm.
3. The pad layout is for reference purposes only.

REEL SPECIFICATION

| P/N | PKG | QTY |
|-------------------|---------|------|
| 1N4001WS-1N4007WS | SOD-323 | 3000 |

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